

IDS 10/24/2000

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Form PTO-1449 U.S. Department of Commerce (Rev. 8-83) Patent and Trademark Office		Attorney Docket No. 0756-2230	Serial No. 08/818,884
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant: Shunpei YAMAZAKI, et al.	
		Filing Date: September 5, 2000	Group: 2871
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Examiner		Date Considered	
DN WLEN		9/18/04	